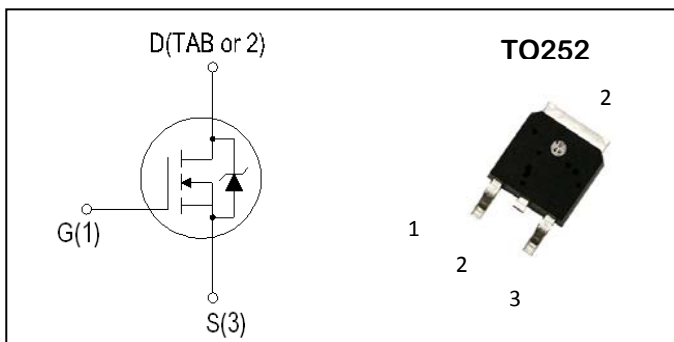


N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V_{DSS}	I_D	$R_{DS(ON)}$ (m Ω)
60V	18A	40m Ω



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Ratings	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	18	A
Mounted on Large Heat Sink				
I _{DM}	300μs Pulse Drain Current Tested(1)	T _C =25°C	40	A
I _D	Continuous Drain Current	T _C =25°C	18	A
		T _C =70°C	13	A
P _D	Maximum Power Dissipation	T _C =25°C	31.3	W

1. Pulse width limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
R_{thJC}	Thermal resistance junction-case max	4	$^\circ\text{C/W}$
R_{thJA}	Thermal resistance junction-ambient max	62	$^\circ\text{C/W}$

Electrical Characteristics (TA=25°C Unless Otherwise Noted)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
On/off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250uA	60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 48V, V _{GS} =0V	--	--	1	uA
		V _{DS} =48V, V _{GS} =0V T _J =55°C	--	--	5	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250uA	1	1.5	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
R _{DS(ON)}	Drain-SourceOn-stateResistance(2)	V _{GS} = 10V, I _{DS} =10A	--	42	55	mΩ
g _{FS}	Forward transconductance(2)	V _{DS} = 5V, I _{DS} =15A	--	25.3	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} =0V,	--	1027	--	pF
C _{oss}	Output Capacitance	V _{DS} = 15V,	--	65	--	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	--	46	--	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time(1)	V _{DD} =30V,	--	2.8	--	ns
t _r	Turn-on Rise Time(1)	I _D = 15A, V _{GS} = 10V,	--	16.6	--	
t _{d(OFF)}	Turn-off Delay Time(1)	R _{GEN} =3.3 Ω	--	21.2	--	
t _f	Turn-off Fall Time(1)		--	5.6	--	
Q _g	Total Gate Charge(1)	V _{DS} =48V, V _{GS} = 10V,	--	19	--	nC
Q _{gs}	Gate-Source Charge(1)	I _{DS} =15A	--	2.5	--	
Q _{gd}	Gate-Drain Charge(1)		--	5	--	
Diode Characteristics						
V _{SD}	Diode Forward Voltage(2)	I _{SD} = 1A, V _{GS} = 0	--	--	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =15A, dI _{SD} /dt=100A/μs	--	12.2	--	ns
q _{rr}	Reverse Recovery Charge		--	7.3	--	nC

NOTES:

1. Independent of operating temperature.
2. Pulse Test : Pulse width ≤ 300 μs, Duty cycle ≤ 2%

Typical Performance Characteristics

Figure 1: On-Region Characteristics

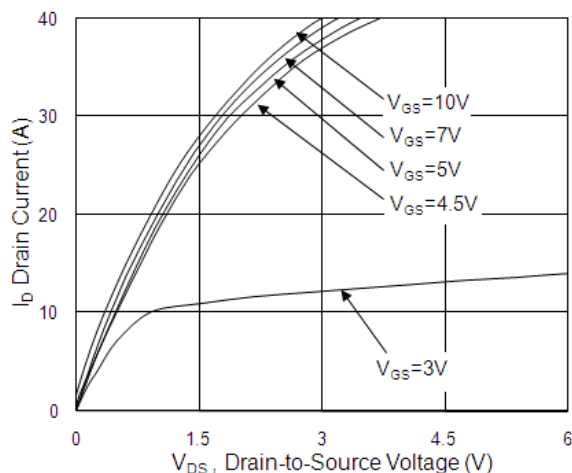


Figure 2: On-Resistance vs. Gate-Source

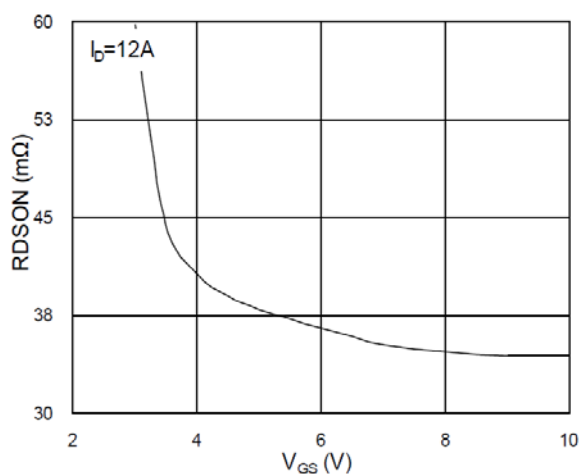


Figure 3: Forward Characteristics Of Reverse

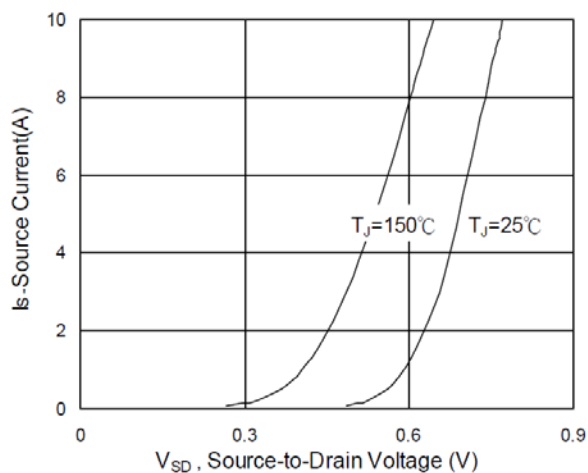


Figure 4: Normalized RDSON vs. TJ

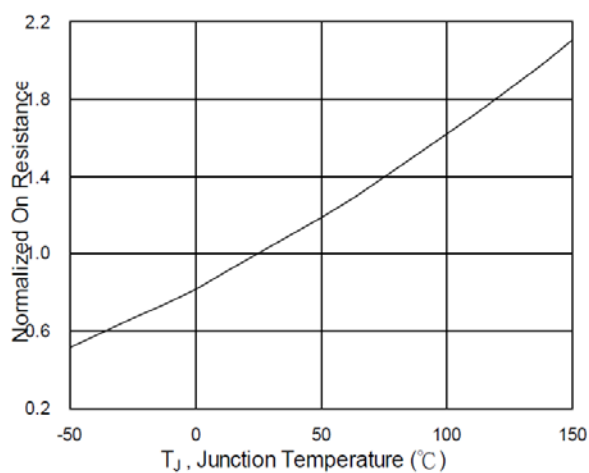


Figure 5: Capacitance Characteristics

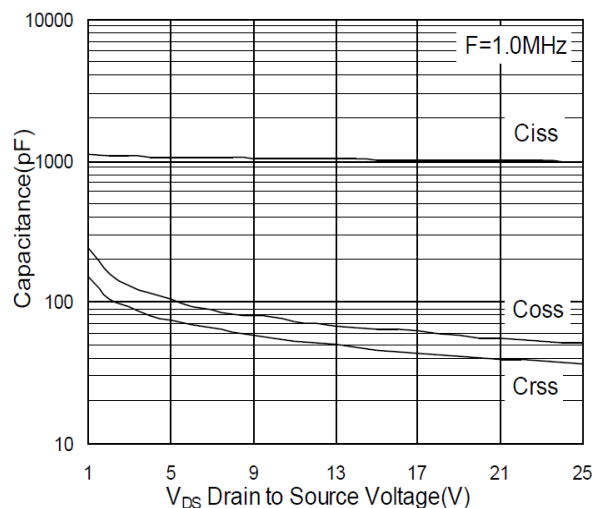


Figure 6: Gate Charge Characteristics

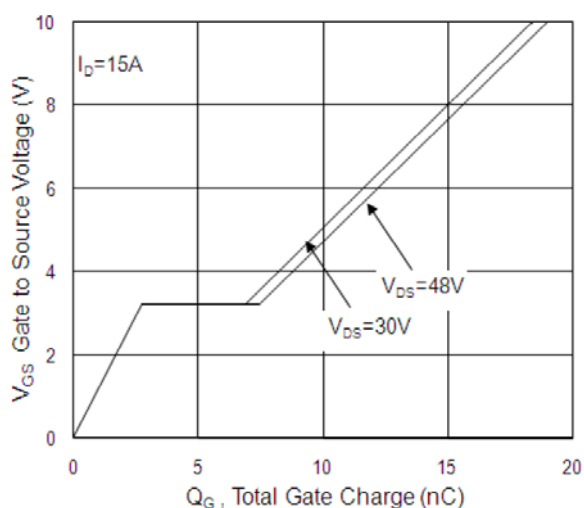


Figure 7: Normalized VGS(th) vs. TJ

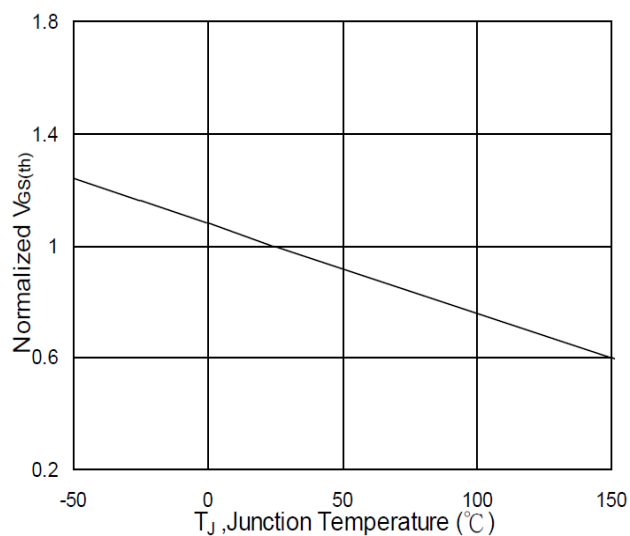


Figure 8: Maximum Safe Operating Area

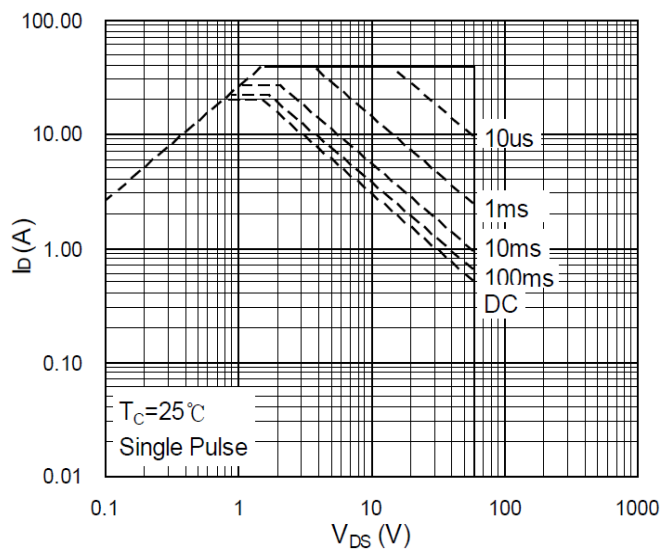
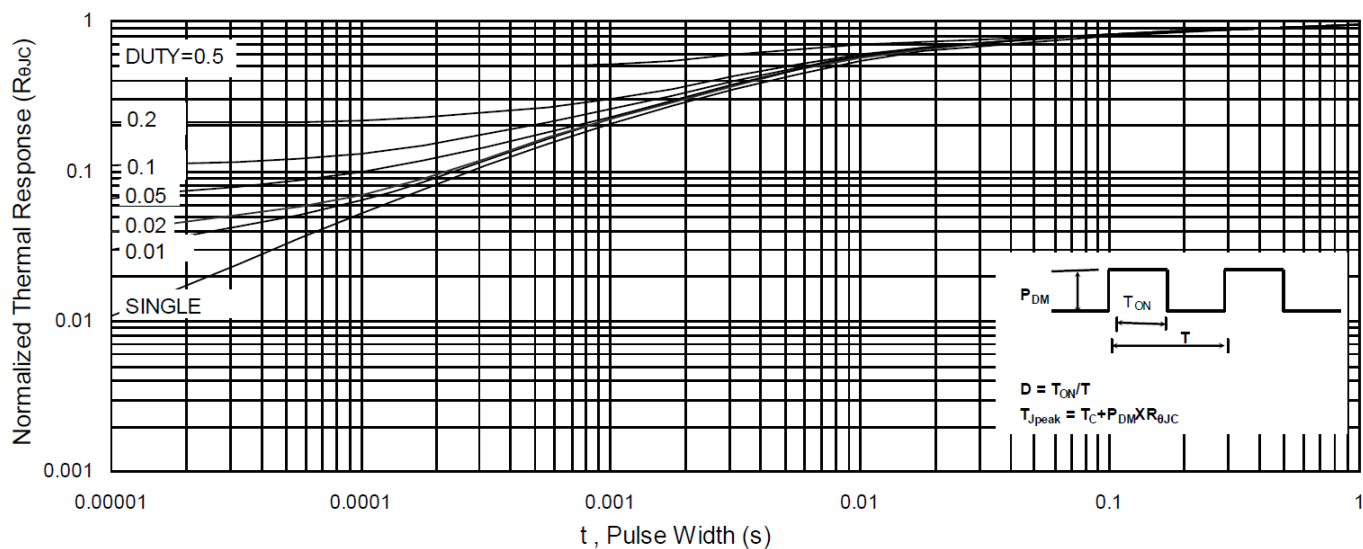
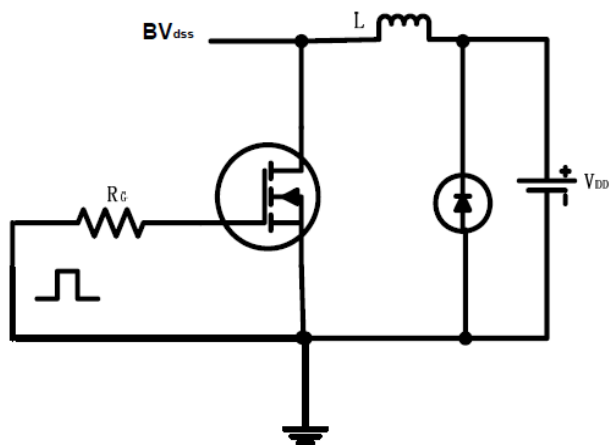


Figure 11. Normalized Maximum Transient Thermal Impedance

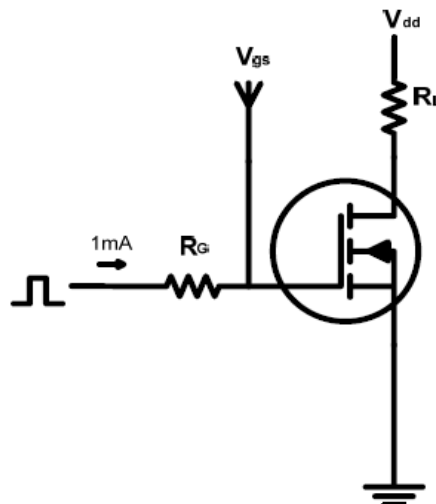


Test circuits and Waveforms

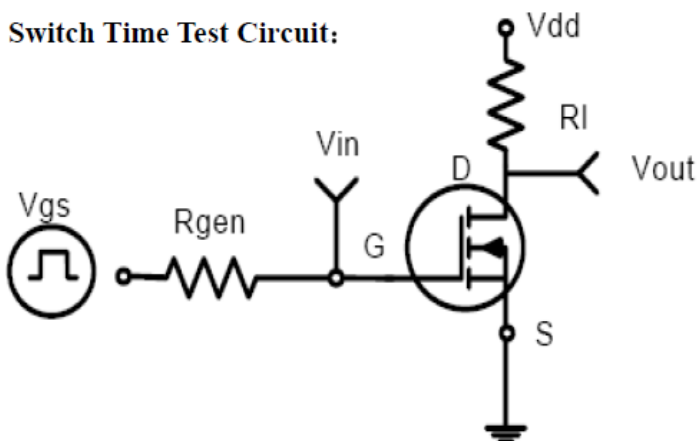
EAS test circuits:



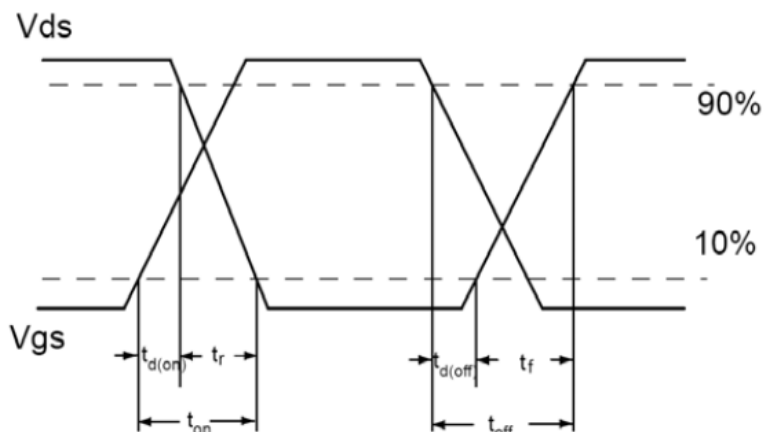
Gate charge test circuit:



Switch Time Test Circuit:

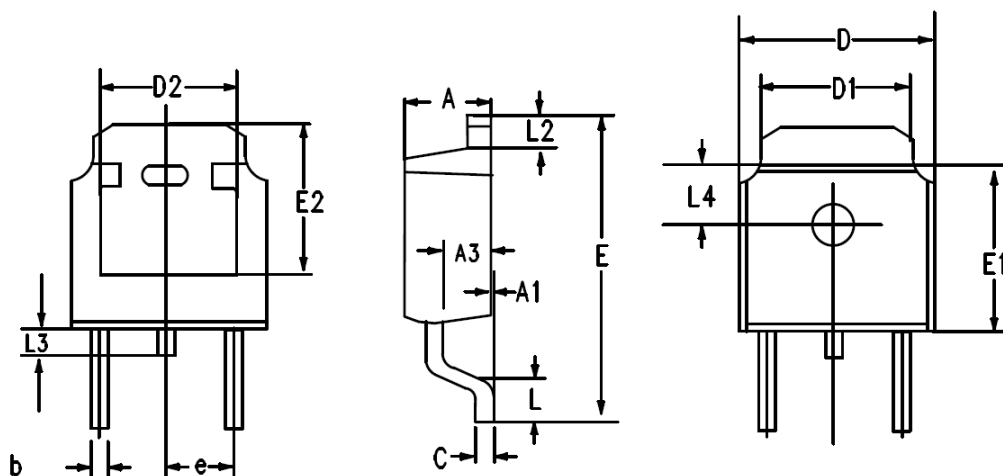


Switch Waveforms:



PACKAGE MECHANICAL DATA

TO-252 Package Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
A3	1.020	1.120	0.040	0.044
b	0.740	0.820	0.029	0.032
c	0.510	0.580	0.020	0.023
D	6.500	6.700	0.256	0.263
D1	5.200	5.400	0.205	0.213
D2	4.830REF.		0.190REF.	
E	9.900	10.300	0.390	0.405
E1	6.000	6.200	0.236	0.244
E2	5.300 REF.		0.208 REF.	
e	2.286TYP.		0.090 TYP.	
L	1.400	1.600	0.055	0.063
L2	0.900	1.250	0.035	0.049
L3	0.600	1.000	0.024	0.039
L4	1.700	1.900	0.066	0.075